TEXAS INSTRUMENTS

SCCS042 - September 1994 - Revised March 2000

8-Bit Latched Transceiver

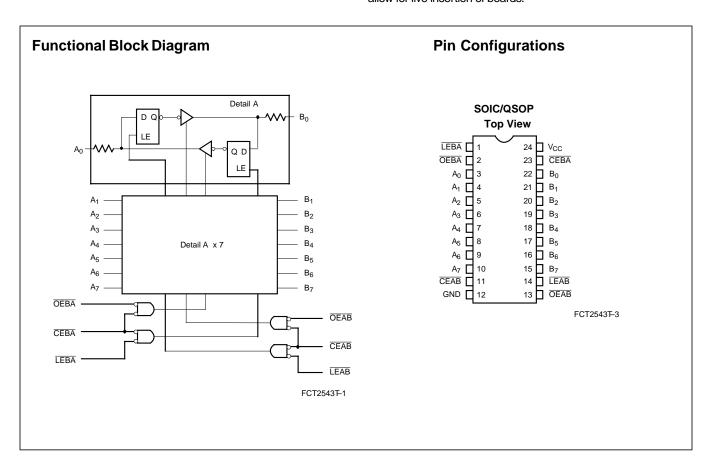
Features

- Function and pinout compatible with FCT and F logic
- FCT-C speed at 5.3 ns max. FCT-A speed at 6.5 ns max.
- 25 $\!\Omega$ output series resistors to reduce transmission line reflection noise
- Reduced V_{OH} (typically = 3.3V) versions of equivalent FCT functions
- Edge-rate control circuitry for significantly improved noise characteristics
- · Power-off disable feature
- · Matched rise and fall times
- Fully compatible with TTL input and output logic levels
- Sink current 12 mA
 Source current 15 mA
- · Separation controls for data flow in each direction
- · Back to back latches for storage
- ESD > 2000V
- Extended commercial temp. range of -40°C to +85°C

Functional Description

The FCT2543T Octal Latched Tranceiver contains two sets of eight D-type latches. Separate Latch Enable ($\overline{\text{LEAB}}$, $\overline{\text{LEBA}}$) and Output Enable ($\overline{\text{OEAB}}$, $\overline{\text{OEBA}}$) permits each latch set to have independent control of inputting and outputting in either direction of data flow. For data flow from A to B, for example, the A-to-B Enable (CEAB) input must be LOW to enter data from A or to take data from B, as indicated in the truth table. With CEAB LOW, a LOW signal on the A-to-B Latch Enable (LEAB) input makes the A-to-B latches transparent; a subsequent LOW-to-HIGH transition of the LEAB signal puts the A latches in the storage mode and their output no longer change with the A inputs. With CEAB and OEAB both LOW, the three-state B output buffers are active and reflect data present at the output of the A latches. Control of data from B to A is similar, but uses CEAB, LEAB, and OEAB inputs. On-chip termination resistors have been added to the outputs to reduce system noise caused by reflections. The FCT2543T can be used to replace the FCT543T to reduce noise in an existing design.

The outputs are designed with a power-off disable feature to allow for live insertion of boards.





Pin Description

Name	Description
OEAB	A-to-B Output Enable Input (Active LOW)
OEBA	B-to-A Output Enable Input (Active LOW)
CEAB	A-to-B Enable Input (Active LOW)
CEBA	B-to-A Enable Input (Active LOW)
LEAB	A-to-B Latch Enable Input (Active LOW)
LEBA	B-to-A Latch Enable Input (Active LOW)
Α	A-to-B Data Inputs or B-to-A Three-State Outputs
В	B-to-A Data Inputs or A-to-B Three-State Outputs

Function Table^[1,2]

Inputs			Inputs Latch	
CEAB	LEAB	OEAB	A-to-B ^[3]	В
Н	Х	Х	Storing	High Z
Х	Н	Х	Storing	Х
Х	Х	Н	Х	High Z
L	L	L	Transparent	Current A Inputs
L	Н	L	Storing	Previous A Inputs

Maximum Ratings^[4,5]

(Above which the useful life may be impaired. For user guidelines, not tested.)
Storage Temperature65°C to +150°C
Ambient Temperature with Power Applied65°C to +135°C
Supply Voltage to Ground Potential0.5V to +7.0V
DC Input Voltage0.5V to +7.0V
DC Output Voltage0.5V to +7.0V
DC Output Current (Maximum Sink Current/Pin) 120 mA
Power Dissipation
Static Discharge Voltage>2001V (per MIL-STD-883, Method 3015)

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	-40°C to +85°C	5V ± 5%

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	Min.	Typ. ^[7]	Max.	Unit
V _{OH}	Output HIGH Voltage	V _{CC} =Min., I _{OH} =-15 mA	2.4	3.3		V
V _{OL}	Output LOW Voltage	V _{CC} =Min., I _{OL} =12 mA		0.3	0.55	V
R _{OUT}	Output Resistance	V _{CC} =Min., I _{OL} =12 mA	20	25	40	Ω
V _{IH}	Input HIGH Voltage		2.0			V
V _{IL}	Input LOW Voltage				0.8	V
V _H	Hysteresis ^[8]	All inputs		0.2		V
V _{IK}	Input Clamp Diode Voltage	V _{CC} =Min., I _{IN} =-18 mA		-0.7	-1.2	V
I _{IH}	Input HIGH Current	V _{CC} =Max., V _{IN} =V _{CC}			5	μΑ
I _{IH}	Input HIGH Current	V _{CC} =Max., V _{IN} =2.7V			±1	μΑ
I _{IL}	Input LOW Current	V _{CC} =Max., V _{IN} =0.5V			±1	μΑ
l _{OZH}	Off State HIGH-Level Output Current	V _{CC} =Max., V _{OUT} =2.7V			15	μА
I _{OZL}	Off State LOW-Level Output Current	V _{CC} =Max., V _{OUT} =0.5V			-15	μА
I _{OS}	Output Short Circuit Current ^[9]	V _{CC} =Max., V _{OUT} =0.0V	-60	-120	-225	mA
I _{OFF}	Power-Off Disable	V _{CC} =0V, V _{OUT} =4.5V			±1	μΑ

Notes:

- H = HIGH Voltage Level. L = LOW Voltage Level. X = Don't Care.
 A-to-B data flow shown: B-to-A is the same, except using CEBA, LEBA, and OEBA.
 Before LEAB LOW-to-HIGH transition.
 Unless otherwise noted, these limits are over the operating free-air temperature range.
 Unused inputs must always be connected to an appropriate logic voltage level, preferably either V_{CC} or ground.
- 6. T_A is the "instant on" case temperature.



Capacitance^[8]

Parameter	Description	Test Conditions	Typ. ^[7]	Max.	Unit
C _{IN}	Input Capacitance		5	10	pF
C _{OUT}	Output Capacitance		9	12	pF

Power Supply Characteristics

Parameter	Description	Test Conditions	Typ. ^[7]	Max.	Unit
I _{CC}	Quiescent Power Supply Current	V _{CC} =Max., V _{IN} ≤0.2V, V _{IN} ≥V _{CC} -0.2V	0.1	0.2	mA
Δl _{CC}	Quiescent Power Supply Current (TTL inputs)	V _{CC} =Max., V _{IN} =3.4V, ^[10] f ₁ =0, Outputs Open	0.5	2.0	mA
I _{CCD}	Dynamic Power Supply Current ^[11]	V _{CC} =Max., One Input Toggling, 50% Duty Cycle, Outputs Open, CEAB and OEAB=LOW, CEBA=HIGH, V _{IN} ≤0.2V or V _{IN} ≥V _{CC} −0.2V	0.06	1.2	mA/ MHz
I _C	Total Power Supply Current ^[12]	$\begin{array}{c} V_{CC}\text{=}Max., f_0\text{=}10\text{MHz}, 50\%\text{Duty}\text{Cycle}, \text{Outputs}\\ \text{Open}, \text{ One Bit Toggling at }f_1\text{=}5\text{MHz},\\ \hline \text{CEAB and }\overline{\text{OEAB}}\text{=}\text{LOW}, \overline{\text{CEBA}}\text{=}\text{HIGH},\\ f_0\text{=}\overline{\text{LEAB}}\text{=}10\text{MHz}, V_{\text{IN}}\text{\le}0.2\text{V or }V_{\text{IN}}\text{\ge}V_{\text{CC}}\text{-}0.2\text{V} \end{array}$	0.7	1.4	mA
		V _{CC} =Max., f ₀ =10 MHz, 50% Duty Cycle, Outputs Open, One Bit Toggling at f ₁ =5 MHz, CEAB and OEAB=LOW, CEBA=HIGH, f ₀ =LEAB =10 MHz, V _{IN} =3.4V or V _{IN} =GND	1.2	3.4	mA
		$\begin{array}{c} V_{CC}\text{=}Max., f_0\text{=}10\text{ MHz}, 50\%\text{ Duty Cycle, Outputs} \\ \text{Open, Eight Bits Toggling at } f_1\text{=}5\text{ MHz}, \\ \hline \text{CEAB and OEAB}\text{=}LOW, \overline{\text{CEBA}}\text{=}HIGH, \\ f_0\text{=}\overline{\text{LEAB}}\text{=}10\text{ MHz}, V_{\text{IN}}\text{\le}0.2\text{V or } V_{\text{IN}}\text{\ge}V_{\text{CC}}\text{-}0.2\text{V} \end{array}$	2.8	5.6 ^[13]	mA
		$\begin{array}{c} V_{CC}\text{=}\text{Max.,} f_0\text{=}10\text{MHz,} 50\%\text{Duty}\text{Cycle,}\text{Outputs}\\ \underline{\text{Open,}}\text{Eight}\underline{\text{Bits}}\text{Toggling}\text{at}f_1\text{=}5\text{MHz,}\\ \underline{\text{CEAB}}\text{and}\overline{\text{OEAB}}\text{=}\text{LOW,}\overline{\text{CEBA}}\text{=}\text{HIGH,}\\ f_0\text{=}\overline{\text{LEAB}}\text{=}10\text{MHz,}V_{\text{IN}}\text{=}3.4\text{V or}V_{\text{IN}}\text{=}\text{GND} \end{array}$	5.1	14.6 ^[13]	mA

Notes:

- Typical values are at V_{CC}=5.0V, T_A=+25°C ambient.
- Typical values are at V_{CC}=5.0V, 1_A=+20 C ambient.
 This parameter is specified but not tested.
 Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parametrics tests. In any sequence of parameter tests, I_{OS} tests should be performed last.
 Per TTL driven input (V_{IN}=3.4V); all other inputs at V_{CC} or GND.

- - D_H = Duty Cycle for TTL inputs HIGH
 N_T = Number of TTL inputs at D_H = Number of TTL inputs at D_H
- NT = Number of TTL Inputs at D_H

 I_{CCD} = Dynamic Current caused by an input transition pair (HLH or LHL)

 f₀ = Clock frequency for registered devices, otherwise zero

 f₁ = Input signal frequency

 N₁ = Number of inputs changing at f₁

 All currents are in milliamps and all frequencies are in megahertz.

 Values for these conditions are examples of the I_{CC} formula. These limits are specified but not tested.



Switching Characteristics Over the Operating Range^[14]

		CY74FC	Г2543Т	CY74FCT	2543AT	CY74FCT2543CT			
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Unit	Fig. No. ^[15]
t _{PLH} t _{PHL}	Propagation Delay Transparent Mode A to B or B to A	2.5	8.5	2.5	6.5	2.5	5.5	ns	1, 3
t _{PLH} t _{PHL}	Propagation Delay LEBA to A LEAB to B	2.5	12.5	2.5	8.0	2.5	7.0	ns	1, 5
t _{PZH} t _{PZL}	Output Enable Time OEBA or OEAB to A or B CEBA or CEAB to A or B	2.0	12.0	2.0	9.0	2.0	8.0	ns	1, 7, 8
t _{PZH} t _{PZL}	Output Disable Time OEBA or OEAB to A or B CEBA or CEAB to A or B	2.0	9.0	2.0	7.5	2.0	6.5	ns	1, 7, 8
t _S	Set-Up Time HIGH or LOW, A or B to LEBA or LEAB	2.0		2.0		2.0		ns	9
t _H	Hold Time HIGH or LOW, A or B to LEBA or LEAB	2.0		2.0		2.0		ns	9
t _W	Pulse Width LOW LEBA or LEAB	5.0		5.0		5.0		ns	5

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
5.3	CY74FCT2543CTQCT	Q13	24-Lead (150-Mil) QSOP	Commercial
	CY74FCT2543CTSOC/SOCT	S13	24-Lead (300-Mil) Molded SOIC	
6.5	CY74FCT2543ATQCT	Q13	24-Lead (150-Mil) QSOP	Commercial
	CY74FCT2543ATSOC/SOCT	S13	24-Lead (300-Mil) Molded SOIC	
8.5	CY74FCT2543TQCT	Q13	24-Lead (150-Mil) QSOP	Commercial

Notes:

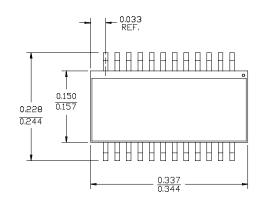
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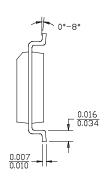
^{14.} Minimum limits are specified but not tested on Propagation Delays.15. See "Parameter Measurement Information" in the General Information section.

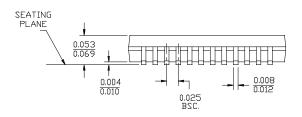


Package Diagrams

24-Lead Quarter Size Outline Q13

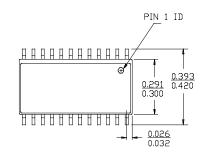




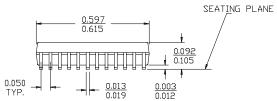


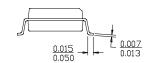
DIMENSIONS IN INCHES $\frac{\text{MIN.}}{\text{MAX.}}$ LEAD COPLANARITY 0.004 MAX.

24-Lead (300-Mil) Molded SOIC S13



DIMENSIONS IN INCHES MIN. MAX.
LEAD COPLANARITY 0.004 MAX.





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